

MOSFET - Power, Single N-Channel, WDFN6 30 V, 4.9 - 18.9 mΩ, 17.2 A

NTLJS3D9N03C

Features

- Small Footprint (4 mm²) for Compact Design
- Low R_{DS(on)} to Minimize Conduction Losses
- These Devices are Pb-Free, Halogen-Free/BFR-Free and are RoHS Compliant

Applications

- Wireless Chargers
- Power Load Switch
- Power Management and Protection
- Battery Management

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	30	V
Gate-to-Source Voltage			V _{GS}	±12	V
Continuous Drain Current R _{θJA} (Notes 1, 3)	Steady State	T _A = 25°C	I _D	17.2	A
		T _A = 85°C		12.4	
Power Dissipation R _{θJA} (Notes 1, 3)		T _A = 25°C	P _D	2.40	W
Continuous Drain Current R _{θJA} (Notes 2, 3)	Steady State	T _A = 25°C	I _D	10.3	A
		T _A = 85°C		7.4	
Power Dissipation R _{θJA} (Notes 2, 3)		T _A = 25°C	P _D	0.86	W
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	71	A
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +150	°C
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 1)	R _{θJA}	52	°C/W
Junction-to-Ambient - Steady State (Note 2)	R _{θJA}	145	

1. Surface-mounted on FR4 board using 1 in² pad size, 2 oz. Cu pad.
2. Surface-mounted on FR4 board using minimum pad size, 2 oz. Cu pad.
3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted. Actual continuous current will be limited by thermal & electro-mechanical application board design. R_{θCA} is determined by the user's board design.

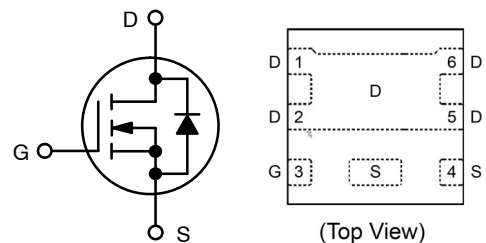


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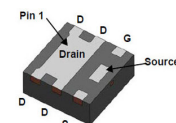
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V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
30 V	4.9 mΩ @ 4.5 V	17.2 A
	6.8 mΩ @ 3.3 V	
	10 mΩ @ 2.5 V	
	18.9 mΩ @ 1.8 V	

ELECTRICAL CONNECTION



N-CHANNEL MOSFET



WDFN6 (2.05x2.05)
CASE 483AV

MARKING DIAGRAM

YWZZ
A3D9

YW = Date Code
ZZ = Assembly Lot Code
A = Assembly Site Code
A3D9 = Specific Device Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 250 μA, ref to 25°C		24.5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1	μA
			T _J = 125°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.6		1.1	V
Threshold Temperature Coefficient	V _{GS} /T _J	I _D = 250 μA, ref to 25°C		-3.83		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		3.6	4.9	mΩ
		V _{GS} = 3.3 V, I _D = 5 A		4.1	6.8	
		V _{GS} = 2.5 V, I _D = 4 A		5.4	10	
		V _{GS} = 1.8 V, I _D = 2 A		9.8	18.9	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 10 A		69		S
Gate Resistance	R _G	T _A = 25°C		1.65		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 15 V, f = 1.0 MHz		1565		pF
Output Capacitance	C _{oss}			677		
Reverse Transfer Capacitance	C _{rss}			54.8		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 10 A		14.7		nC
Threshold Gate Charge	Q _{G(TH)}			1.17		nC
Gate-to-Source Charge	Q _{GS}			2.31		
Gate-to-Drain Charge	Q _{GD}			3.29		

SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 5)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DD} = 15 V, I _D = 10 A, R _G = 6 Ω		10.1		ns
Rise Time	t _r			9.5		
Turn-Off Delay Time	t _{d(off)}			40.6		
Fall Time	t _f			15.4		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.75	1.2	V
			T _J = 125°C		0.611		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 10 A			31.7		ns
Reverse Recovery Charge	Q _{RR}				11.2		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

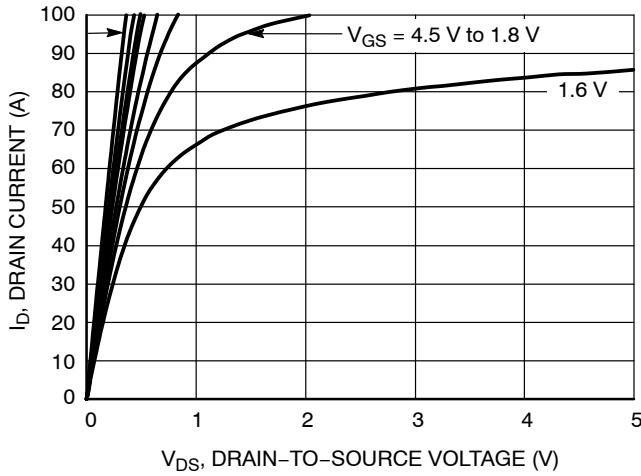


Figure 1. On-Region Characteristics

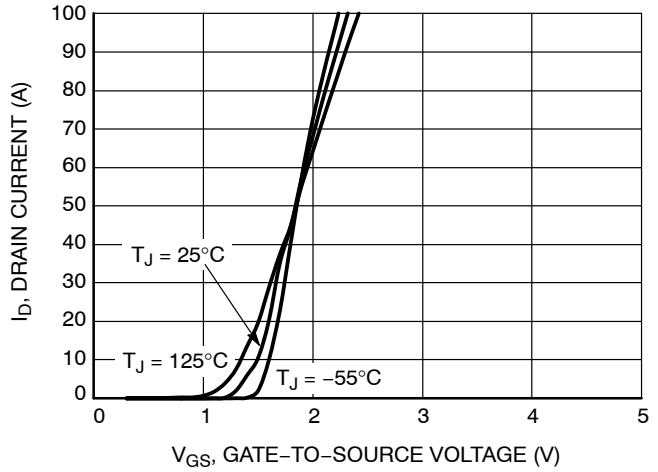


Figure 2. Transfer Characteristics

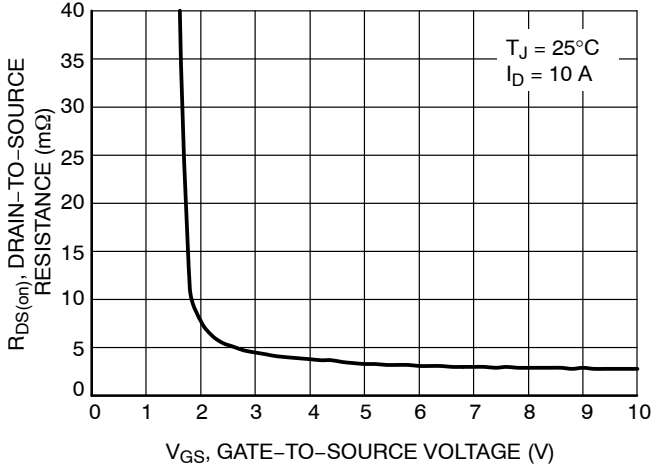


Figure 3. On-Resistance vs. Gate-to-Source Voltage (V)

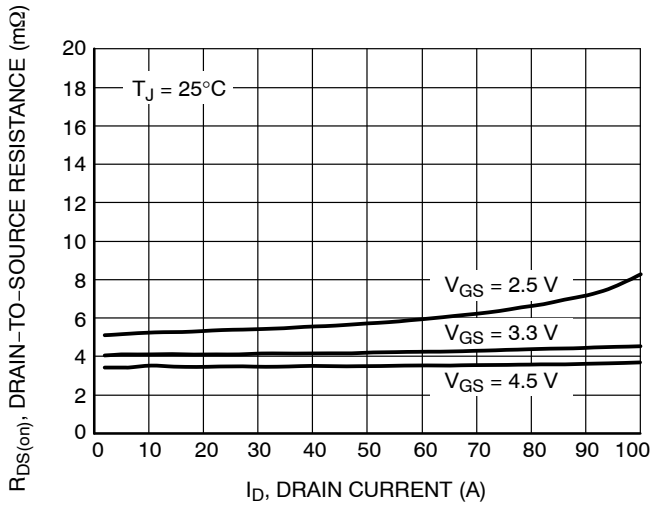


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

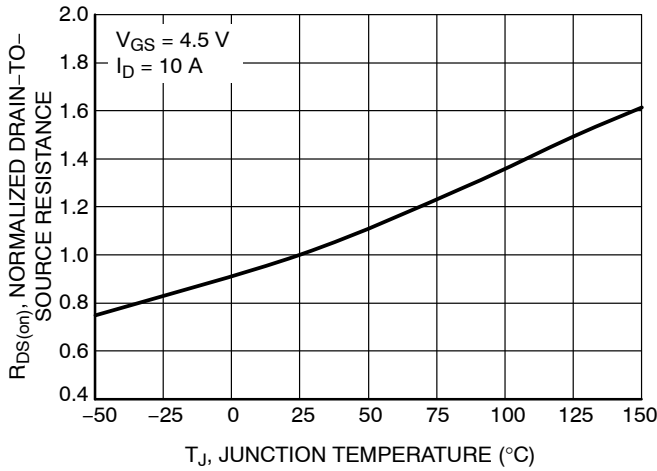


Figure 5. On-Resistance Variation with Temperature

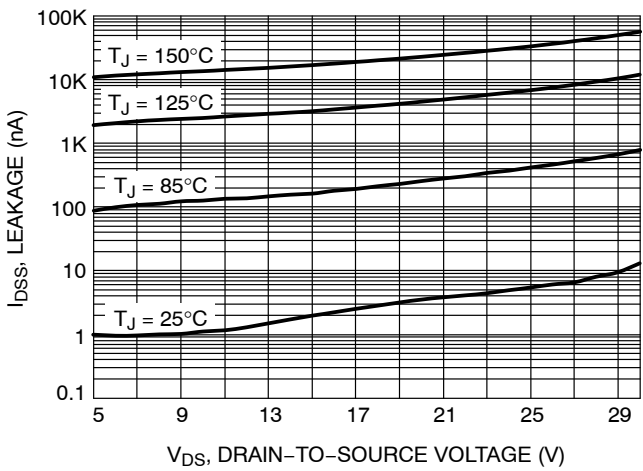


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

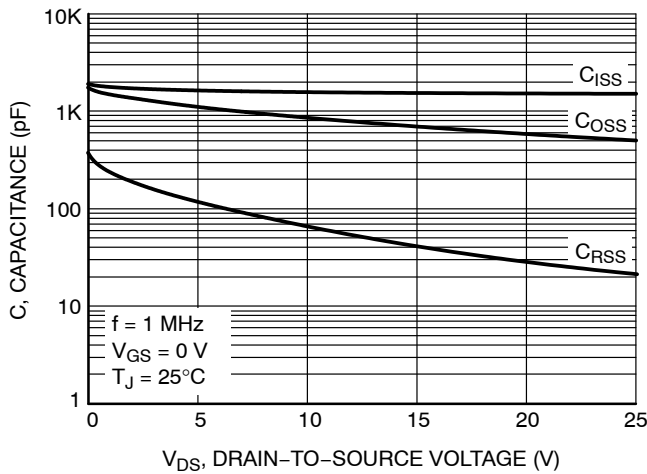


Figure 7. Capacitance Variation

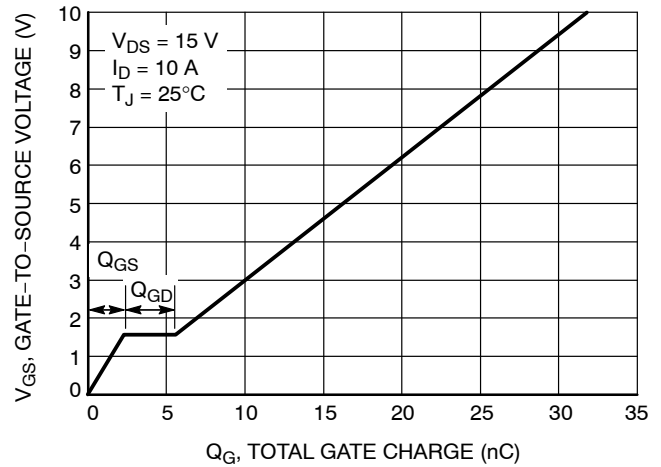


Figure 8. Gate-to-Source vs. Total Charge

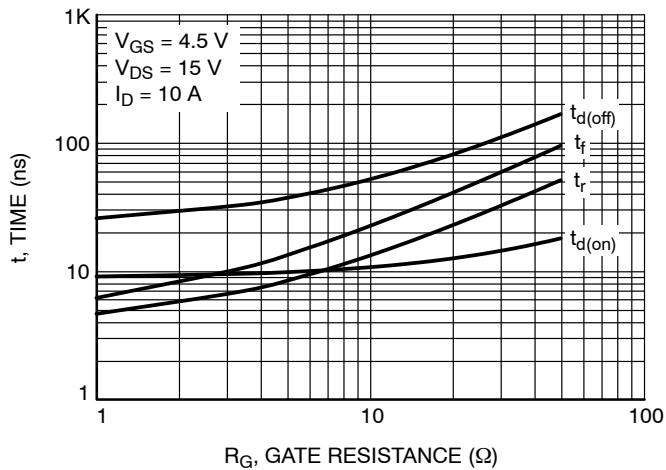


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

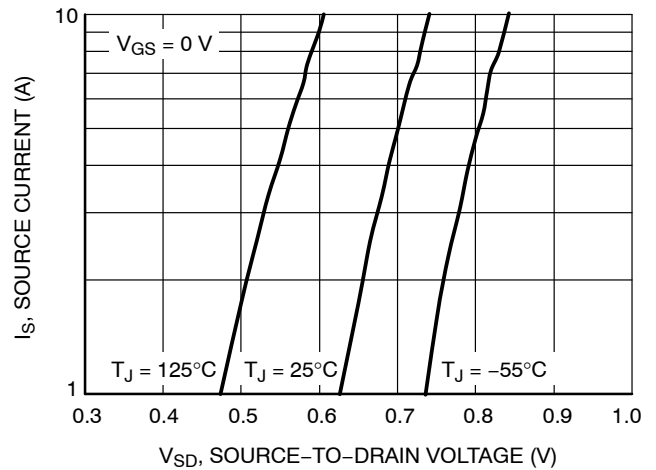


Figure 10. Diode Forward Voltage vs. Current

DEVICE ORDERING INFORMATION

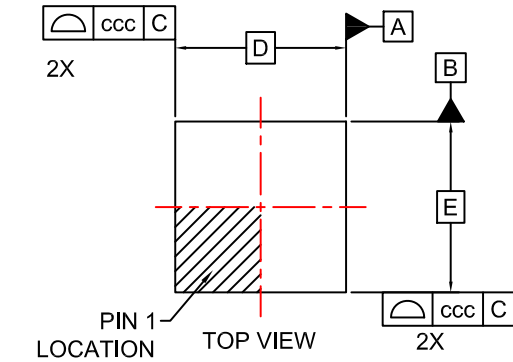
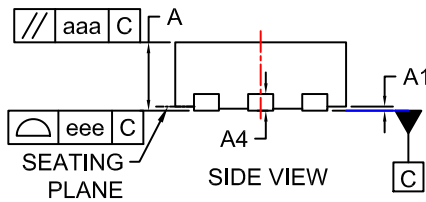
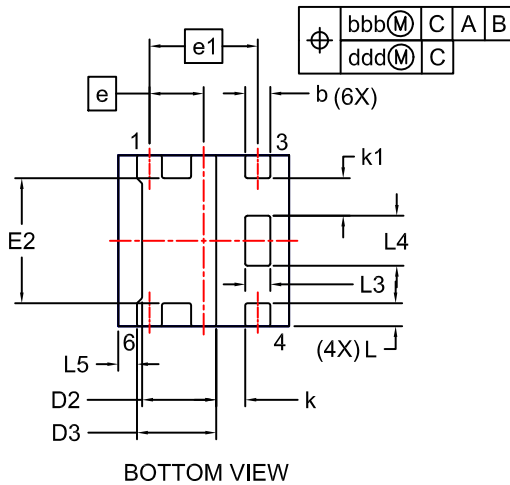
Device	Package	Shipping†
NTLJS3D9N03CTAG	WDFN6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

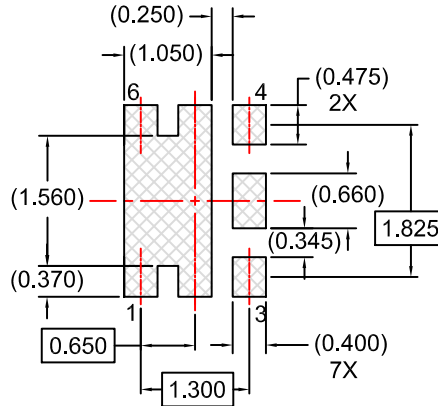
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PACKAGE DIMENSIONS

WDFN6 2.05X2.05, 0.65P
CASE 483AV
ISSUE A



LAND PATTERN RECOMMENDATION



NOTES:

1. CONTROLLING DIMENSION: MILLIMETERS.
2. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.60	0.70	0.80
A1	0.00	-	0.05
A4	(0.20)		
b	0.25	0.30	0.35
D	1.95	2.05	2.15
D2	0.84	0.89	0.94
D3	(0.95)		
E	1.95	2.05	2.15
E2	1.45	1.50	1.55
e	0.65 BSC		
e1	1.30 BSC		
k	(0.35)		
k1	(0.45)		
L	0.18	0.28	0.38
L3	0.25	0.30	0.35
L4	0.55	0.60	0.65
L5	(0.23)		
aaa	0.10		
bbb	0.10		
ccc	0.05		
ddd	0.05		
eee	0.05		

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